

# Schottky barrier diode

## RB425D / RB421D

### ●Applications

Low power rectification

### ●Features

- 1) Small surface mounting type. (SMD3)
- 2) Low  $V_F$ . ( $V_F=0.45V$  Typ. at 100mA)
- 3) High reliability.

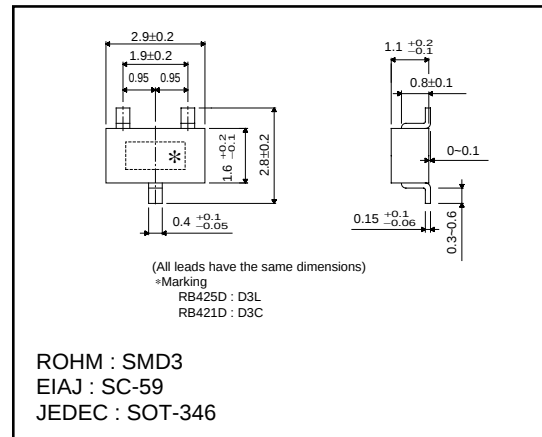
### ●Construction

Silicon epitaxial planar

### ●Marking

|        |  |
|--------|--|
| RB425D |  |
| RB421D |  |

### ●External dimensions (Units : mm)

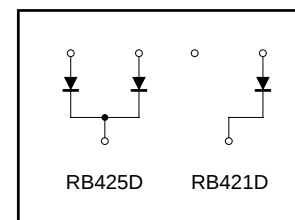


### ●Absolute maximum ratings ( $T_a = 25^\circ C$ )

| Parameter                   | Symbol    | Limits   | Unit       |
|-----------------------------|-----------|----------|------------|
| Peak reverse voltage        | $V_{RM}$  | 40       | V          |
| DC reverse voltage          | $V_R$     | 40       | V          |
| Mean rectifying current     | $I_O$     | 0.1      | A          |
| Peak forward surge current* | $I_{FSM}$ | 1        | A          |
| Junction temperature        | $T_J$     | 125      | $^\circ C$ |
| Storage temperature         | $T_{stg}$ | -40~+125 | $^\circ C$ |

\* 60Hz for 1

### ●Circuit



### ●Electrical characteristics ( $T_a = 25^\circ C$ )

| Parameter                     | Symbol   | Min. | Typ. | Max. | Unit    | Conditions        |
|-------------------------------|----------|------|------|------|---------|-------------------|
| Forward voltage               | $V_{F1}$ | —    | —    | 0.55 | V       | $I_F=100mA$       |
| Forward voltage               | $V_{F2}$ | —    | —    | 0.34 | V       | $I_F=10mA$        |
| Reverse current               | $I_R$    | —    | —    | 30   | $\mu A$ | $V_R=10V$         |
| Capacitance between terminals | $C_T$    | —    | 6.0  | —    | pF      | $V_R=10V, f=1MHz$ |

Note) ESD sensitive product handling required.

## Diodes

●Electrical characteristic curves ( $T_a = 25^\circ\text{C}$ )